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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PBSS4140T 40 V, 1A NPN low V_{CEsat} (BISS) transistor

Product data sheet Supersedes data of 2005 Feb 14 2005 Feb 24



40 V, 1A NPN low V_{CEsat} (BISS) transistor

PBSS4140T

FEATURES

- Low collector-emitter saturation voltage
- · High current capabilities.
- Improved device reliability due to reduced heat generation.

APPLICATIONS

- · General purpose switching and muting
- · LCD backlighting
- Supply line switching circuits
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

DESCRIPTION

NPN low V_{CEsat} transistor in a SOT23 plastic package. PNP complement: PBSS5140T.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PBSS4140T	ZT*

Note

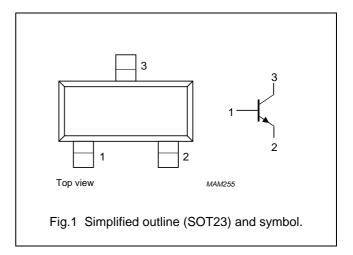
- 1. * = p: made in Hong Kong.
 - * = t: made in Malaysia.
 - * = W: made in China.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	40	V
I _{CM}	peak collector current	2	Α
R _{CEsat}	equivalent on-resistance	<500	mΩ

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE	PACKAGE			
NUMBER	NAME	DESCRIPTION VERSION		
PBSS4140T	-	plastic surface mounted package; 3 leads	SOT23	

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PBSS4140T

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	40	V
V_{CEO}	collector-emitter voltage	open base	-	40	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
Ic	collector current (DC)		_	1	Α
I _{CM}	peak collector current		-	2	Α
I _{BM}	peak base current		_	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	300	mW
		T _{amb} ≤ 25 °C; note 2	-	450	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.
- 2. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
R _{th(j-a)}	thermal resistance from junction	in free air; note 1	417	K/W
	to ambient	in free air; note 2	278	K/W

Notes

- 1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
- 2. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm².

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PBSS4140T

CHARACTERISTICS

 T_{amb} = 25 $^{\circ}C$ unless otherwise specified.

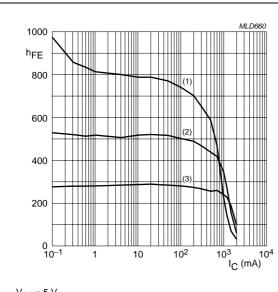
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off	V _{CB} = 40 V; I _E = 0 A	_	_	100	nA
	current	V _{CB} = 40 V; I _E = 0 A; T _{amb} = 150 °C	_	_	50	μΑ
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$	_	_	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A	_	_	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 1 mA	300	_	_	
		V _{CE} = 5 V; I _C = 500 mA	300	_	900	
		V _{CE} = 5 V; I _C = 1 A	200	_	_	
V _{CEsat}	collector-emitter saturation	I _C = 100 mA; I _B = 1 mA	_	_	200	mV
	voltage	$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	_	_	250	mV
		I _C = 1 A; I _B = 100 mA	_	_	500	mV
R _{CEsat}	equivalent on-resistance	$I_C = 500 \text{ mA}$; $I_B = 50 \text{ mA}$; note 1	_	260	<500	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = 1 A; I _B = 100 mA	_	_	1.2	V
V _{BEon}	base-emitter turn-on voltage	V _{CE} = 5 V; I _C = 1 A	_	_	1.1	V
f _T	transition frequency	$I_C = 50 \text{ mA}; V_{CE} = 10 \text{ V}; f = 100 \text{ MHz}$	150	_	_	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A}; f = 1 \text{ MHz}$	_	_	10	pF

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

40 V, 1A NPN low V_{CEsat} (BISS) transistor

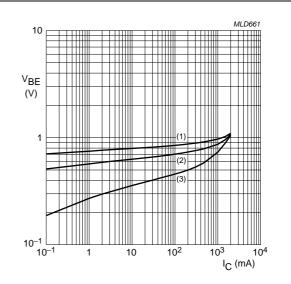
PBSS4140T



 $V_{CE} = 5 V$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

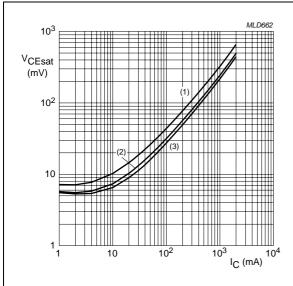
Fig.2 DC current gain as a function of collector current; typical values.



 $V_{CE} = 5 V.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) T_{amb} = 25 °C.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

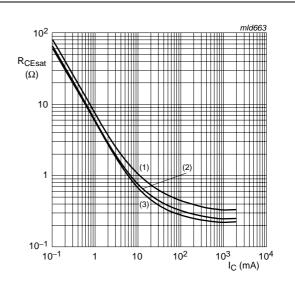
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.5 Equivalent on-resistance as a function of collector current; typical values.

2005 Feb 24 5

40 V, 1A NPN low V_{CEsat} (BISS) transistor

PBSS4140T

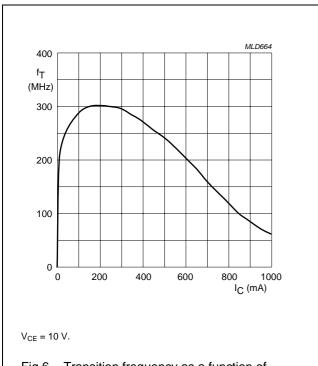


Fig.6 Transition frequency as a function of collector current.

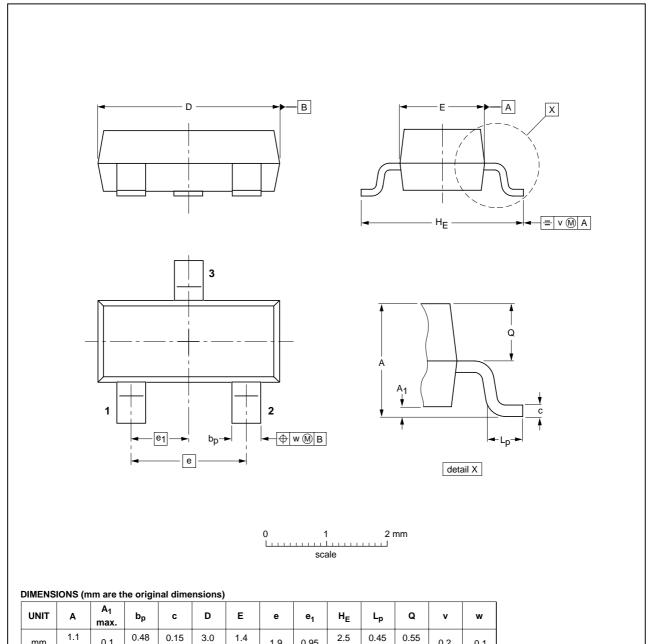
40 V, 1A NPN low V_{CEsat} (BISS) transistor

PBSS4140T

PACKAGE OUTLINE



SOT23



OUTLINE	REFERENCES		EUROPEAN	IOOUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION ISSUE DAT	
SOT23		TO-236AB				-04-11-04 06-03-16

0.1

1.9

2005 Feb 24 7

0.38

0.9

40 V, 1A NPN low V_{CEsat} (BISS) transistor

PBSS4140T

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
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PBSS4140T,235 PBSS4140T,215